NSN 5961-01-195-1317



Transistor - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-01-195-1317 **Inclosure Material:** Metal **Overall Length:** 1.330 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-61 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.687 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 breakdown voltage, collector-to-base, emitter open and 9.0 breakdown voltage, emitter-to-base, collector open and 400.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 10.00 amperes source cutoff current and 5.00 amperes source cutoff current **Power Rating Per Characteristic:** 125.0 watts small-signal input power, common-collector absolute **Transfer Ratio:** 35.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab, solder lug Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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